Unit in mm

TOSHIBA FIELD EFFECT TRANSISTOR SILICON N CHANNEL JUNCTION TYPE

2 S K 1 1 7

LOW NOISE AUDIO AMPLIFIER APPLICATIONS

• High $|Y_{fs}|$: $|Y_{fs}| = 15 \text{mS (Typ.)}$

 $(V_{DS}=10V, V_{GS}=0)$

• High Breakdown Voltage: VGDS=-50V

• Low Noise : NF=1.0dB (Typ.) (V_{DS}=10V,

 $I_D = 0.5 \text{mA}$, f = 1 kHz, $R_G = 1 \text{k}\Omega$)

• High Input Impedance : $I_{GSS} = -1nA \text{ (Max.) } (V_{GS} = -30V)$

MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT	
Gate-Drain Voltage	v_{GDS}	-50	V	
Gate Current	$I_{\mathbf{G}}$	10	mA	
Drain Power Dissipation	P_{D}	300	mW	
Junction Temperature	T_j	125	$^{\circ}\mathrm{C}$	
Storage Temperature Range	${f T}_{ m stg}$	-55~125	$^{\circ}\mathrm{C}$	

1. DRAIN 2. GATE 3. SOURCE JEDEC TO-92 EIAJ SC-43 TOSHIBA 2-5F1D

Weight: 0.21g

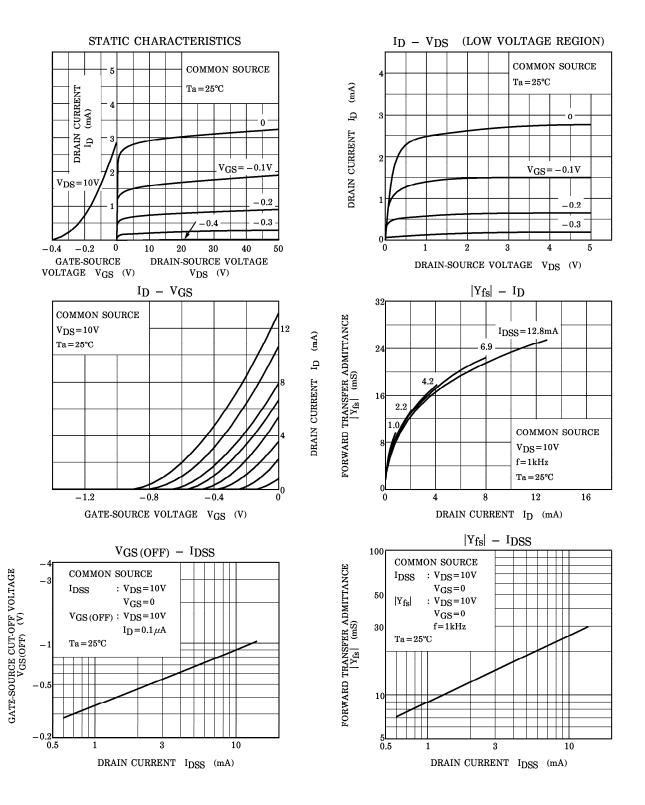
ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Gate Cut-off Current	I_{GSS}	$V_{GS} = -30V, V_{DS} = 0$	_	_	-1.0	nА
Gate-Drain Breakdown Voltage	V _(BR) GDS	$V_{DS} = 0$, $I_G = -100 \mu A$	-50	_	_	V
Drain Current	I _{DSS} (Note)	$V_{DS}=10V, V_{GS}=0$	1.2	_	14	mA
Gate-Source Cut-off Voltage	$V_{ m GS(OFF)}$	$V_{DS} = 10V, I_{D} = 0.1 \mu A$	-0.2	_	-1.5	V
Forward Transfer Admittance	$ Y_{fs} $	$V_{ m DS}\!=\!10{ m V},~V_{ m GS}\!=\!0,~{ m f}\!=\!1{ m kHz}$	4.0	15	_	mS
Input Capacitance	C_{iss}	$V_{DS} = 10V, V_{GS} = 0, f = 1MHz$	_	13	_	pF
Reverse Transfer Capacitance	C _{rss}	$V_{GD} = -10V, I_D = 0, f = 1MHz$	_	3	_	pF
Noise Figure	NF (1)	V_{DS} =10V, R_G =1k Ω I_D =0.5mA, f=10Hz	_	5	10	- dB
	NF (2)	V_{DS} =10V, R_{G} =1k Ω I_{D} =0.5mA, f=1kHz	_	1	2	ub

Note : I_{DSS} Classification Y : 1.2~3.0mA, GR : 2.6~6.5mA, BL : 6~14mA

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